	Application No. Applicant(s)			
	09/921,423	THAKUR ET AL.A	THAKUR ET AL.A	
Notice of Allowability	Examiner	Art Unit		
	Johannes P Mondt	2826	الهم	
The MAILING DATE of this communication app All claims being allowable, PROSECUTION ON THE MERITS IS herewith (or previously mailed), a Notice of Allowance (PTOL-85 NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT F of the Office or upon petition by the applicant. See 37 CFR 1.31	S (OR REMAINS) CLOSED in b) or other appropriate commu RIGHTS. This application is so	this application. If not included nication will be mailed in due co	ourse. THIS	
1. X This communication is responsive to After-Final Amendm	ent filed 7/13/04.			
2. ⊠ The allowed claim(s) is/are <u>1-9 and 11-12</u> .				
3. $igotimes$ The drawings filed on <u>17 March 2003</u> are accepted by the	e Examiner.			
4. ☐ Acknowledgment is made of a claim for foreign priority u a) ☐ All b) ☐ Some* c) ☐ None of the:		r (f).		
1. Certified copies of the priority documents hav		a No		
2. Certified copies of the priority documents hav			n franciska	
3. Copies of the certified copies of the priority do	ocuments have been received	in this national stage application	n irom the	
International Bureau (PCT Rule 17.2(a)).				
* Certified copies not received:				
Applicant has THREE MONTHS FROM THE "MAILING DATE" noted below. Failure to timely comply will result in ABANDON! THIS THREE-MONTH PERIOD IS NOT EXTENDABLE.		a reply complying with the requi	irements	
5. A SUBSTITUTE OATH OR DECLARATION must be subm INFORMAL PATENT APPLICATION (PTO-152) which give			TICE OF	
6. CORRECTED DRAWINGS (as "replacement sheets") mu	st be submitted.			
(a) ☐ including changes required by the Notice of Draftsper	son's Patent Drawing Review	(PTO-948) attached		
1) 🗌 hereto or 2) 🔲 to Paper No./Mail Date	_•			
(b) ☐ including changes required by the attached Examiner Paper No./Mail Date	's Amendment / Comment or	in the Office action of		
Identifying indicia such as the application number (see 37 CFR each sheet. Replacement sheet(s) should be labeled as such in			ack) of	
 DEPOSIT OF and/or INFORMATION about the deposit attached Examiner's comment regarding REQUIREMENT 			te the	
Attachment(s)		•		
1. ☑ Notice of References Cited (PTO-892)	5. Notice of Info	ormal Patent Application (PTO-	152)	
2. Notice of Draftperson's Patent Drawing Review (PTO-948)	_	mmary (PTO-413), ⁄lail Date		
 Information Disclosure Statements (PTO-1449 or PTO/SB/0 Paper No./Mail Date 		Amendment/Comment		
4. Examiner's Comment Regarding Requirement for Deposit	8. 🛛 Examiner's S	Statement of Reasons for Allowa	ance _	
of Biological Material	9. 🗌 Other	. chmh	bouts	
		Minhloan	Tran	
		Primary Exa Art Unit 2		

U.S. Patent and Trademark Office PTOL-37 (Rev. 1-04)

EXAMINER'S AMENDMENT

1. An examiner's amendment to the record appears below. Should the changes and/or additions be unacceptable to applicant, an amendment may be filed as provided by 37 CFR 1.312. To ensure consideration of such an amendment, it MUST be submitted no later than the payment of the issue fee.

Authorization for this examiner's amendment was given in a telephone interview with Attorney J. Duzan on July 26, 2004.

BEGIN EXAMINER'S AMENDMENT

Claim 11: the wording "said at least one dielectric layer" (lines 1-2) has been replaced by "said at least one layer of dielectric material".

Claim 12: the wording "said conductive layer" (lines 1-2) has been replaced by "said at least one electrode layer".

END EXAMINER'S AMENDMENT

REASONS FOR ALLOWANCE

Claims 1-9 and 11-12 are allowed.

1. The following is an examiner's statement of reasons for allowance:

a semiconductor memory device with capacitor cell wherein at least one layer of germanium boro-phospho silicate glass has a portion that is in contact with a layer of boro-phospho silicate glass has not been found in the prior art. Although semiconductor memory device with capacitor cell including either boro-phospho silicate glass or germanium boro-phospho silicate glass as materials along roughened interfaces are known (see, e.g., Ando (6,097,053) or Sandhu et al (6,249,019 B1)), and although

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exploitation of differences in etch rates between abutting layers of silicon oxide layers of different densities in said capacitor cell are known to have been used for creating corrugation and thus yielding enhanced capacitance as witnessed by Hsia et al (5,827,783), the known sensitivity in the dependence of etch rate on germanium content of boro-phospho silicate glass (see Haller (5,804,506), i.e., on *compositional* differences between the abutting layers, does not appear to have been exploited in accordance with claims by Applicant.

Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Johannes P Mondt whose telephone number is 571-272-1919. The examiner can normally be reached on 8:00 - 18:00.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Nathan J Flynn can be reached on 571-272-1915. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

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Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

JPM July 23,2004